

1        Claim 4 (amended):

2        The device according to claim 3, wherein the substrate can be maintained at elevated  
3        temperatures during transition from MOVPE to HVPE.

1        Claim 5 (amended):

2        The device according to claim 2, wherein said device can also transition from HVPE to  
3        MOVPE *in situ*.

1        Claim 6 (amended): The device according to claim 5, wherein said device can also

2        transition from HVPE to MOVPE *in situ*.

1        Claim 7 (amended):

2        The device according to claim 6, wherein the substrate can be maintained at elevated  
3        temperatures during transition from HVPE to MOVPE.

1        Claim 8 (amended):

2        The device according to claim 1, wherein said device can be used to grow a  
3        III-V nitride compound semiconductor onto the surface of the substrate.

1        Claim 9 (amended): The device according to claim 8, wherein said device can be used

2        to grow GaN onto the surface of the substrate.

1        Claim 10 (amended):

2        The device according to claim 9, wherein said means for performing HVPE comprises  
3        a hot wall reactor having a source zone, and

4        a downstream mixing zone,

5        wherein TMG can be reached with Hcl in the source zone to form a chlorinated <sup>G</sup>gallium  
6        species, and wherein the chlorinated <sup>G</sup>gallium species can combine with NH<sub>3</sub> in the downstream  
7        mixing zone and directed toward the substrate for deposition of GaN onto the substrate.

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*A/Conclude*  
*sak*

1 Claim 11 (amended):

2 The device according to claim 9, wherein said means for performing MOVPE comprises

3 a low pressure ~~horizontal~~ cold-wall MOCVD reactor.

*horizontal*

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